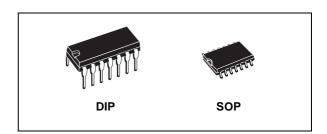




# QUAD EXCLUSIVE-OR GATE

- MEDIUM SPEED OPERATION  $t_{PHL} = t_{PLH} = 65$ ns (TYP.) at  $C_L = 50$ pF and  $V_{DD}$ - $V_{SS} = 10$ V
- LOW OUTPUT IMPEDANCE :  $500 \Omega$  (TYP.) at  $V_{DD}$ - $V_{SS}$  = 10V
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I<sub>I</sub> = 100nA (MAX) AT V<sub>DD</sub> = 18V T<sub>A</sub> = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



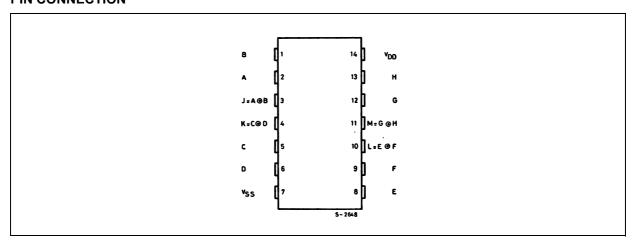
#### **ORDER CODES**

PACKAGE	TUBE	T&R
DIP	HCF4030BEY	
SOP	HCF4030BM1	HCF4030M013TR

#### **DESCRIPTION**

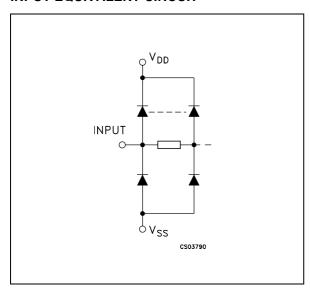
HCF4030B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. HCF4030B types consist of four indipendent exclusive-OR gates integrated on a single monolithic silicon chip. Each exclusive-OR gate consists of four n-channel and four p-channel enhancement-type transistors. All inputs and outputs are protected against electrostatic effects.

# PIN CONNECTION



September 2002 1/10

# **INPUT EQUIVALENT CIRCUIT**



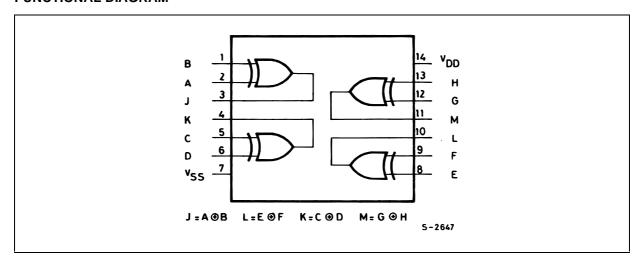
# **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
2, 1, 5, 6, 8, 9, 12, 13	A, B, C, D, E, F, G, H	Data Inputs
3, 4, 10, 11	J, K, L, M	Data Outputs
7	$V_{SS}$	Negative Supply Voltage
14	$V_{DD}$	Positive Supply Voltage

# **TRUTH TABLE**

IN1	IN2	OUT
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

### **FUNCTIONAL DIAGRAM**



### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	-0.5 to +22	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
II	DC Input Current	± 10	mA
P <sub>D</sub>	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T <sub>op</sub>	Operating Temperature	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V<sub>SS</sub> pin voltage.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	3 to 20	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

### **DC SPECIFICATIONS**

			Test Con	dition		Value							
Symbol	Parameter	VI	v <sub>o</sub>	I <sub>O</sub>	$V_{DD}$	Т	<sub>A</sub> = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	<b>(μΑ)</b>	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.02	4		4		30	
		0/10			10		0.02	8		8		60	μΑ
		0/15			15		0.02	16		16		120	μΑ
		0/20			20		0.04	20		20		600	
V <sub>OH</sub>	Output High	0/5		<1	5	4.95			4.95		4.95		
	Voltage	0/10		<1	10	9.95			9.95		9.95		V
		0/15		<1	15	14.95			14.95		14.95		
V <sub>OL</sub>	Output Low Voltage	5/0		<1	5		0.05			0.05		0.05	
		10/0		<1	10		0.05			0.05		0.05	V
		15/0		<1	15		0.05			0.05		0.05	
V <sub>IH</sub>	Input High Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		
			1/9	<1	10	7			7		7		V
			1.5/13.5	<1	15	11			11		11		
V <sub>IL</sub>	Input Low Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	
			9/1	<1	10			3		3		3	V
			13.5/1.5	<1	15			4		4		4	
I <sub>OH</sub>	Output Drive	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		
	Current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		mΑ
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		mA
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I <sub>OL</sub>	Output Sink	0/5	0.4	<1	5	0.44	1		0.36		0.36		
	Current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mΑ
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I <sub>I</sub>	Input Leakage Current	0/18	Any In	put	18		±10 <sup>-5</sup>	±0.1		±1		±1	μΑ
Cl	Input Capacitance		Any In	put			5	7.5					pF

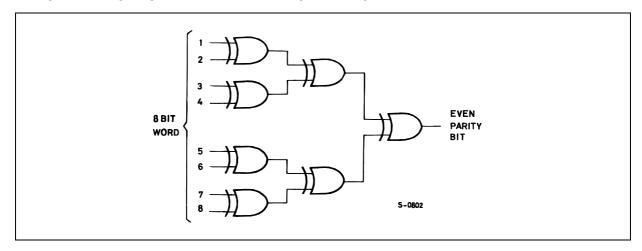
The Noise Margin for both "1" and "0" level is: 1V min. with  $V_{DD}$ =5V, 2V min. with  $V_{DD}$ =10V, 2.5V min. with  $V_{DD}$ =15V

# $\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \; (\textbf{T}_{amb} = 25 ^{\circ} \textbf{C}, \;\; \textbf{C}_{L} = 50 \text{pF}, \; \textbf{R}_{L} = 200 \text{K}\Omega, \;\; \textbf{t}_{r} = \textbf{t}_{f} = 20 \; \text{ns})$

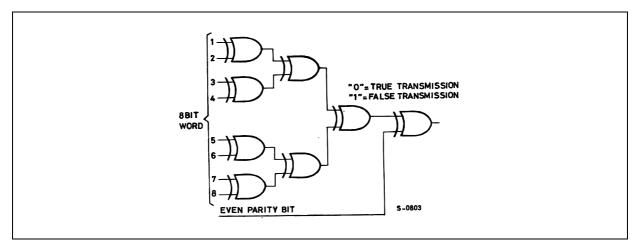
Compleat	Barrantar	Test Condition			Value (*)			
Symbol	Parameter	V <sub>DD</sub> (V)		Min.	Тур.	Max.		
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	5			140	280		
		10			65	130	ns	
		15			50	100		
t <sub>TLH</sub> t <sub>THL</sub>	Output Transition Time	5			100	200		
		10			50	100	ns	
		15			40	80		



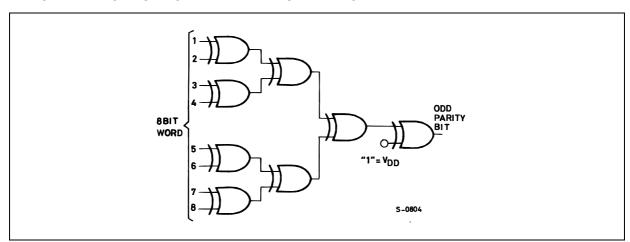
# **TYPICAL APPLICATION:** EVEN PARITY-BIT GENERATOR



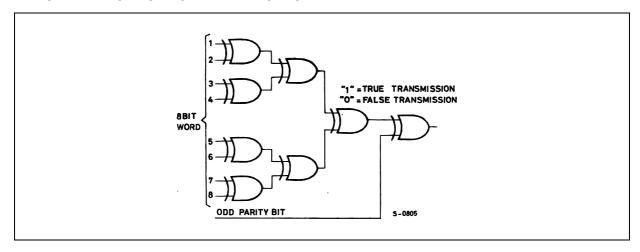
# **TYPICAL APPLICATION:** EVEN PARITY-CHECKER



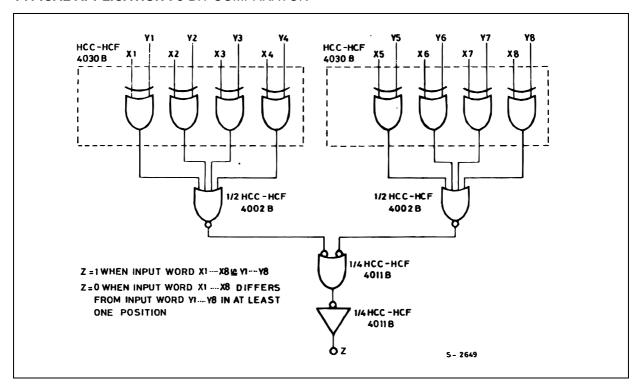
# **TYPICAL APPLICATION: ODD-PARITY-BIT GENERATOR**



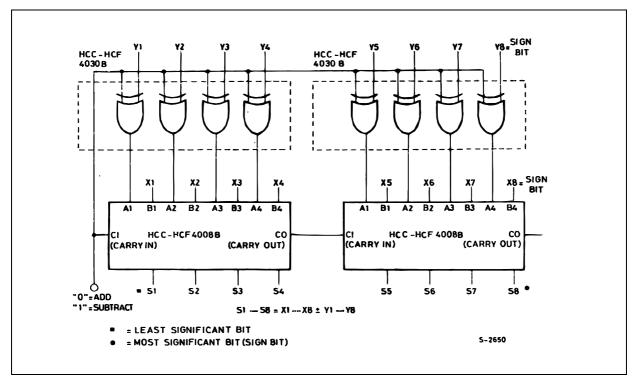
# **TYPICAL APPLICATION: ODD-PARITY-CHECKER**



# **TYPICAL APPLICATION: 8-BIT COMPARATOR**

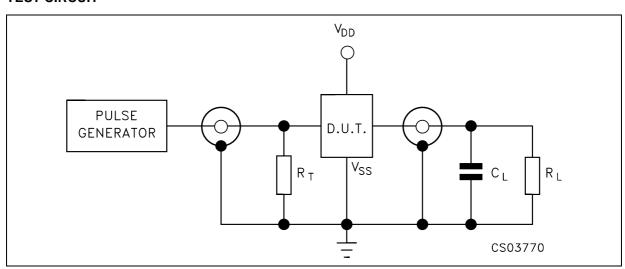


# TYPICAL APPLICATION: 8-BIT TWO'S COMPLEMENT ADDER-SUBSTRACTOR



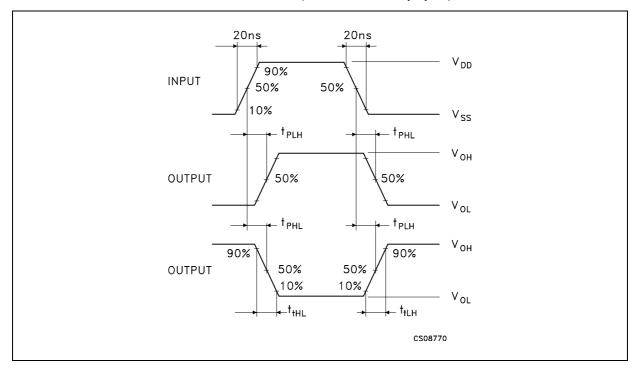
(\*) Typical temperature coefficient for all  $\rm V_{DD}$  value is 0.3 %/°C.

### **TEST CIRCUIT**



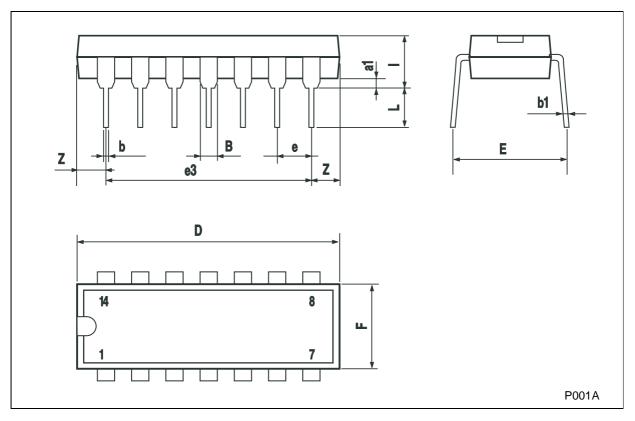
 $C_L$  = 50pF or equivalent (includes jig and probe capacitance)  $R_L$  = 200K $\Omega$   $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

# WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



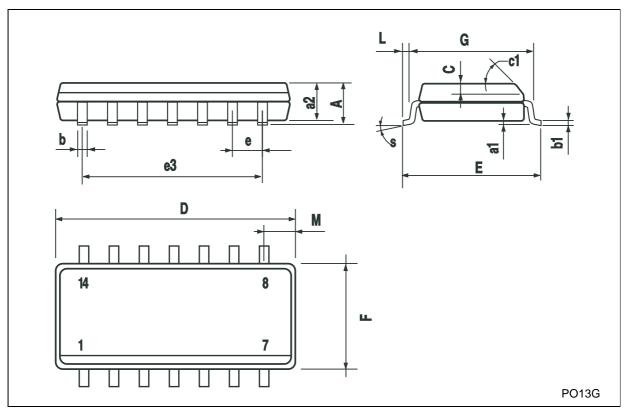
# **Plastic DIP-14 MECHANICAL DATA**

DIM		mm.			inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
a1	0.51			0.020					
В	1.39		1.65	0.055		0.065			
b		0.5			0.020				
b1		0.25			0.010				
D			20			0.787			
E		8.5			0.335				
е		2.54			0.100				
e3		15.24			0.600				
F			7.1			0.280			
I			5.1			0.201			
L		3.3			0.130				
Z	1.27		2.54	0.050		0.100			



# **SO-14 MECHANICAL DATA**

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (1	max.)		•		



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco Singapore - Spain - Sweden - Switzerland - United Kingdom - United States. © http://www.st.com

Downloaded from **Arrow.com.**